

MMBZ27VCWT1G

40 Watt Peak Power Zener Transient Voltage Suppressors

SC-70 Dual Common Cathode Zeners for ESD Protection

These dual monolithic silicon zener diodes are designed for applications requiring transient overvoltage protection capability. They are intended for use in voltage and ESD sensitive equipment such as computers, printers, business machines, communication systems, medical equipment and other applications. Their dual junction common cathode design protects two separate lines using only one package. These devices are ideal for situations where board space is at a premium.

Specification Features:

- SC-70 Package Allows Either Two Separate Unidirectional Configurations or a Single Bidirectional Configuration
- Working Peak Reverse Voltage Range – 22 V
- Standard Zener Breakdown Voltage – 27 V
- Peak Power – 40 W @ 1.0 ms (Bidirectional), per Figure 4 Waveform
- ESD Rating of Class N (exceeding 16 kV) per the Human Body Model
- Low Leakage < 100 nA
- Flammability Rating: UL 94 V-O
- This is a Pb-Free Device

Mechanical Characteristics:

CASE: Void-free, transfer-molded, thermosetting plastic case

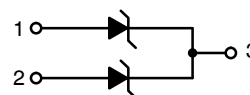
FINISH: Corrosion resistant finish, easily solderable

MAXIMUM CASE TEMPERATURE FOR SOLDERING PURPOSES:
260°C for 10 Seconds



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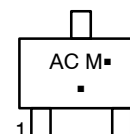


PIN 1. ANODE
2. ANODE
3. CATHODE



SC-70
CASE 419
STYLE 4

MARKING DIAGRAM



AC = Specific Device Code
M = Date Code
▪ = Pb-Free Package
(Note: Microdot may be in either location)

ORDERING INFORMATION

Device	Package	Shipping†
MMBZ27VCWT1G	SC-70 (Pb-Free)	3000/Tape & Reel

† For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

MMBZ27VCWT1G

MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Peak Power Dissipation @ 1.0 ms (Note 1) @ $T_L \leq 25^\circ\text{C}$	P_{pk}	40	Watts
Total Power Dissipation on FR-5 Board (Note 2) @ $T_A = 25^\circ\text{C}$ Derate above 25°C	P_D	200 1.6	mW mW/ $^\circ\text{C}$
Thermal Resistance Junction-to-Ambient	$R_{\theta JA}$	618	$^\circ\text{C}/\text{W}$
Junction and Storage Temperature Range	T_J, T_{stg}	- 55 to +150	$^\circ\text{C}$

Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

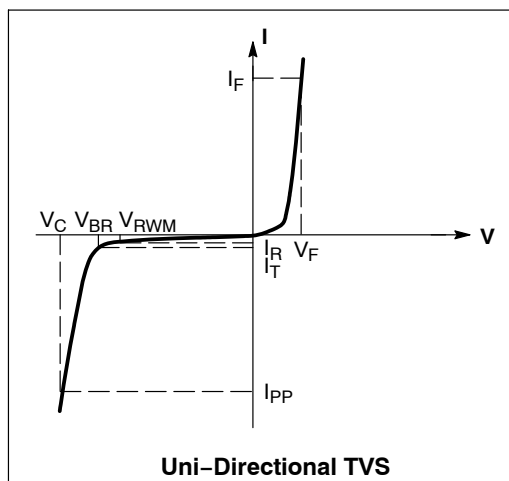
1. Nonrepetitive current pulse per Figure 4 and derate above $T_A = 25^\circ\text{C}$ per Figure 5.
2. FR-5 = 1.0 x 0.75 x 0.62 in.

ELECTRICAL CHARACTERISTICS

($T_A = 25^\circ\text{C}$ unless otherwise noted)

UNIDIRECTIONAL (Circuit tied to Pins 1 and 3 or 2 and 3)

Symbol	Parameter
I_{PP}	Maximum Reverse Peak Pulse Current
V_C	Clamping Voltage @ I_{PP}
V_{RWM}	Working Peak Reverse Voltage
I_R	Maximum Reverse Leakage Current @ V_{RWM}
V_{BR}	Breakdown Voltage @ I_T
I_T	Test Current
V_{BR}	Maximum Temperature Coefficient of V_{BR}
I_F	Forward Current
V_F	Forward Voltage @ I_F



ELECTRICAL CHARACTERISTICS ($T_A = 25^\circ\text{C}$ unless otherwise noted)

UNIDIRECTIONAL (Circuit tied to Pins 1 and 3 or Pins 2 and 3)

($V_F = 1.1 \text{ V Max @ } I_F = 200 \text{ mA}$)

Device	Device Marking	V_{RWM} Volts	$I_R @ V_{RWM}$ nA	Breakdown Voltage			$V_C @ I_{PP}$ (Note 4)		V_{BR} mV/ $^\circ\text{C}$	
				V_{BR} (Note 3) (V)			V_C V	I_{PP} A		
				Min	Nom	Max				@ I_T mA
MMBZ27VCWT1G	AC	22	50	25.65	27	28.35	1.0	38	1.0	26

3. V_{BR} measured at pulse test current I_T at an ambient temperature of 25°C .
4. Surge current waveform per Figure 4 and derate per Figure 5

MMBZ27VCWT1G

TYPICAL CHARACTERISTICS

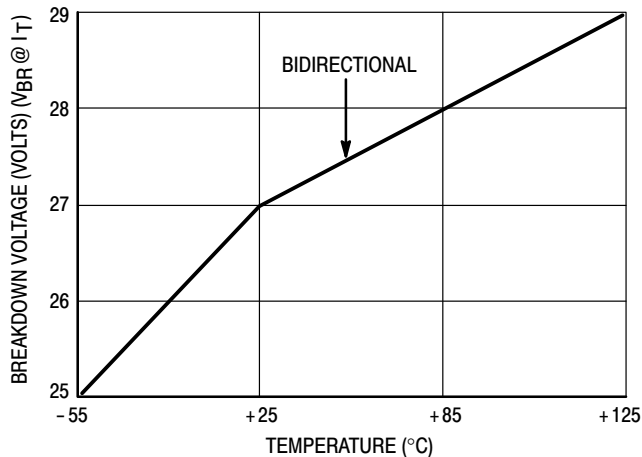


Figure 1. Typical Breakdown Voltage versus Temperature

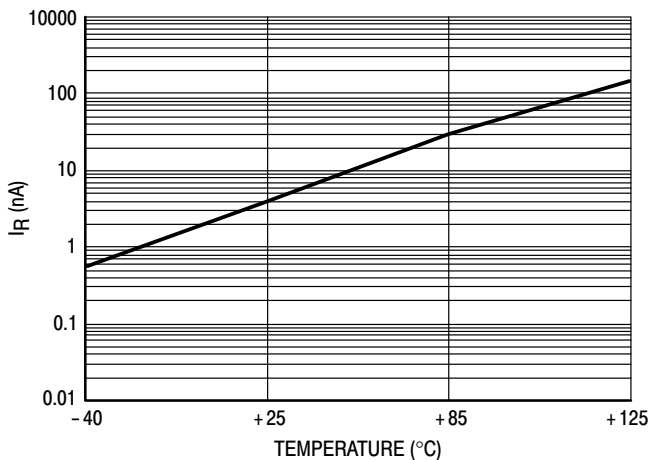


Figure 2. Typical Leakage Current versus Temperature

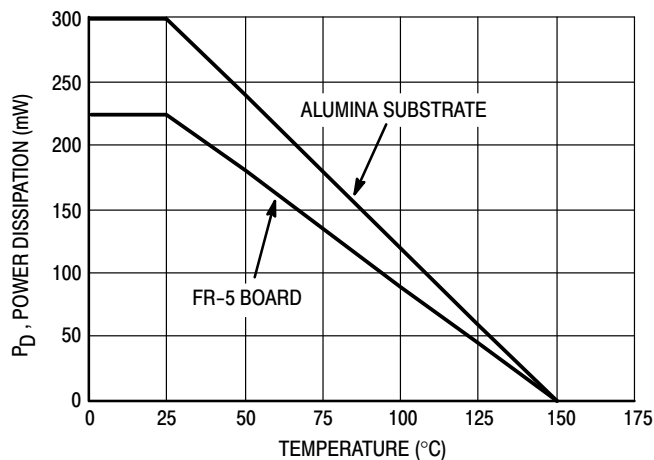


Figure 3. Steady State Power Derating Curve

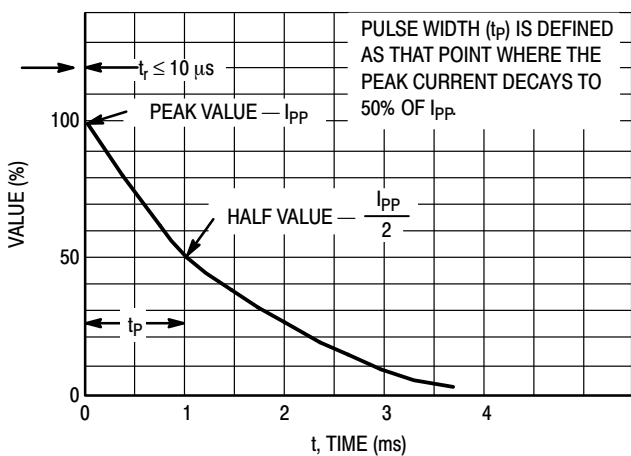


Figure 4. Pulse Waveform

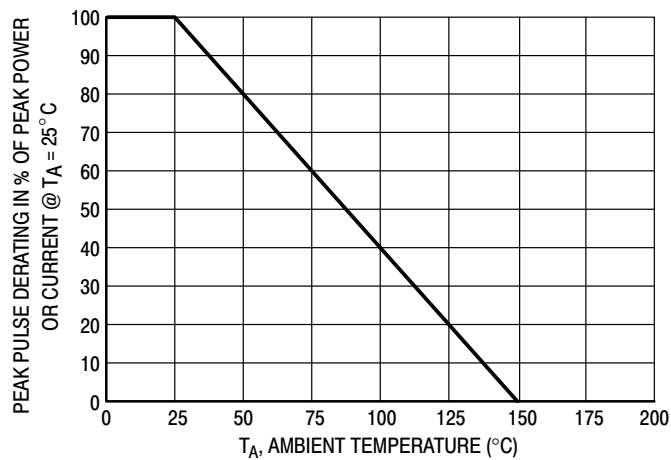
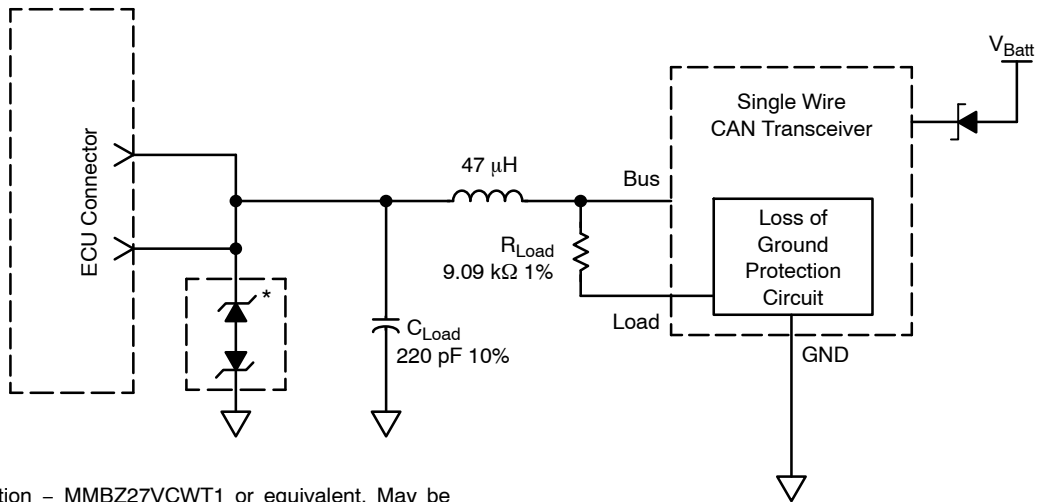


Figure 5. Pulse Derating Curve

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TYPICAL APPLICATIONS



*ESD Protection – MMBZ27VCWT1 or equivalent. May be located in each ECU (C_{Load} needs to be reduced accordingly) or at a central point near the DLC.

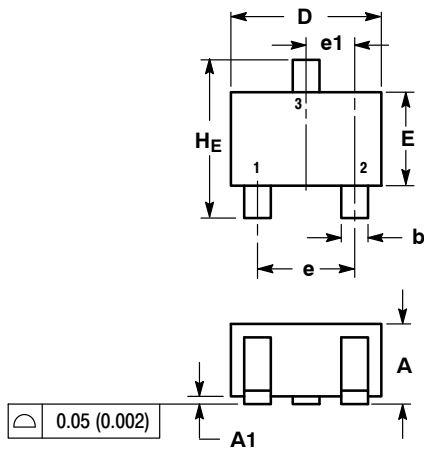
Figure 6. Single Wire CAN Network

Figure is the recommended solution for transient EMI/ESD protection. This circuit is shown in the Society of Automotive Engineers February, 2000 J2411 “Single Wire CAN Network for Vehicle Applications” specification (Figure 6, page 11). Note: the dual common anode zener configuration shown above is electrically equivalent to a dual common cathode zener configuration.

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PACKAGE DIMENSIONS

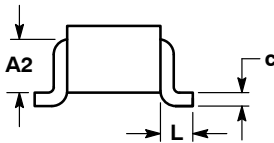
SC-70 (SOT-323)
CASE 419-04
ISSUE M



NOTES:

1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: INCH.

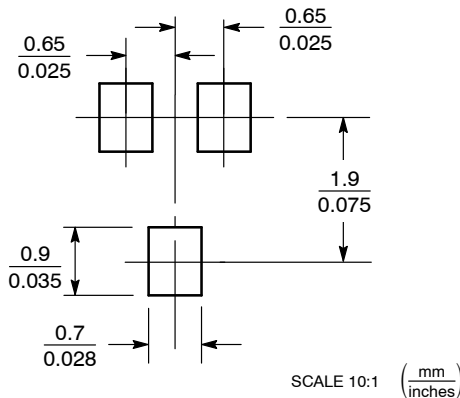
DIM	MILLIMETERS			INCHES		
	MIN	NOM	MAX	MIN	NOM	MAX
A	0.80	0.90	1.00	0.032	0.035	0.040
A1	0.00	0.05	0.10	0.000	0.002	0.004
A2	0.7 REF			0.028 REF		
b	0.30	0.35	0.40	0.012	0.014	0.016
c	0.10	0.18	0.25	0.004	0.007	0.010
D	1.80	2.10	2.20	0.071	0.083	0.087
E	1.15	1.24	1.35	0.045	0.049	0.053
e	1.20	1.30	1.40	0.047	0.051	0.055
e1	0.65 BSC			0.026 BSC		
L	0.425 REF			0.017 REF		
HE	2.00	2.10	2.40	0.079	0.083	0.095



STYLE 4:

1. CATHODE
2. CATHODE
3. ANODE

SOLDERING FOOTPRINT*



*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

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